

ELEG 340 - Fall 08
Solid-State Electronics
Quiz 2

9 October 2008

NAME

Solution

Time Limit: 30 minutes

Closed Books and Notes. You may use your own calculator, but you may not loan or borrow calculators (ask proctor if you have questions). Put expression in a final form as best you can, and indicate final units (dimensions).

Guidelines:

- I. Full credit requires giving the final dimensions/ units for all numerical quantities that you calculate.
- II. Show all work and calculations for full credit.
- III. Accuracy to 2 significant figures is sufficient.
- IV. Assume that the material is silicon at room temperature (300 K or 296 K), unless otherwise stated.
- V. At room temperature (300K), thermal energy $k_B T = 0.0258$ eV (0.026 eV), silicon has intrinsic concentration $n_i = 1$ (or 1.5) $\times 10^{10}$ cm^{-3} . and recombination lifetimes: $\tau_n, \tau_p = 1$ μsec .

Note permittivity of free space $\epsilon_0 = 8.85 \times 10^{-14}$ F/cm; magnitude of electron charge $q = 1.6 \times 10^{-19}$ Coul

VI. Equations:

$$p_{op} = i\hbar d/dx$$

$$f_{FD}(E) = 1/[1 + \exp(E-E_F)/k_B T]$$

$$n = n_i \exp[(E_F - E_i)/k_B T].$$

$$p = n_i \exp[(E_i - E_F)/k_B T]$$

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$$J_n = q\mu_n n \mathcal{E} + qD_n dn/dx$$

$$J_p = q\mu_p p \mathcal{E} - qD_p dp/dx$$

$$U_n = (n_p - n_{p0})/\tau_n$$

$$U_p = (p_n - p_{n0})/\tau_p$$

$$C = \epsilon_s / W$$

$$D/\mu = k_B T/q$$

$$L = \sqrt{(D\tau)}$$

$$E = Q V$$

$$\partial p/\partial t = -1/q \partial J_p/\partial x - p'/\tau_p$$

$$\partial n/\partial t = -1/q \partial J_n/\partial x - n'/\tau_n$$

$$\partial p/\partial t = D_p \partial^2 p/\partial x^2 - p'/\tau_p$$

$$\partial n/\partial t = D_n \partial^2 n/\partial x^2 - n'/\tau_n$$

$$p' = p - p_0 = g_{opt} \tau_p$$

$$n' = n - n_0 = g_{opt} \tau_n$$

1. . An electron has a kinetic energy of 2 eV (electron volt). What is its energy in Joules? For full credit, show your work.

$$W = qV = 1.6 \times 10^{-19} \text{ Coul} \times 2 \text{ V}$$
$$2 \text{ eV} = 3.2 \times 10^{-19} \text{ Joule.}$$

$J = C \times V$

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2. A sample of silicon at room temperature (300K) is uniformly doped with acceptors to a concentration $N_A = 10^{18} \text{ cm}^{-3}$. What is the concentration of holes in the valence band?

$$P = N_A = 10^{18} \text{ cm}^{-3}$$

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3. . The silicon in the question above is now compensation doped with donors $N_D = 2 \times 10^{17} \text{ cm}^{-3}$. What is the new concentration of holes?

$$P = N_A - N_D = 10^{18} \text{ cm}^{-3} - 2 \times 10^{17} \text{ cm}^{-3}$$
$$= 8 \times 10^{17} \text{ cm}^{-3}$$

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4. A wafer of silicon at $T = 300 \text{ K}$ has a free electron concentration of $n = 1 \times 10^{17} \text{ cm}^{-3}$. What is the hole concentration?

$$p = \frac{n_i^2}{n} = \frac{10^{20} \text{ cm}^{-6}}{10^{17} \text{ cm}^{-3}} = 10^3 \text{ cm}^{-3}$$

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5. For the silicon above, calculate the energy of the Fermi level, E_F relative to the intrinsic level, E_i .

$$n = 10^{17} \text{ cm}^{-3} = n_i e^{(E_F - E_i)/kT}$$

$$\begin{aligned} 4 \quad E_F - E_i &= kT \ln \frac{10^{17}}{10^{10}} = 0.026 \ln 10^7 \\ &= 0.26 \times 1.61 = 0.26 + 0.15 \\ &= 0.41 \text{ eV} \end{aligned}$$

6. A sample of GaAs is n-type doped with $N_D = 1 \times 10^{16} \text{ cm}^{-3}$. The electron mobility is $\mu_n = 8500 \text{ cm}^2/\text{V}\cdot\text{s}$. Calculate the electrical conductivity, σ .

$$\begin{aligned} 4 \quad \sigma &= n q \mu = 10^{16} \text{ cm}^{-3} \times 1.6 \times 10^{-19} \text{ C} \times 8.5 \times 10^3 \frac{\text{cm}^2}{\text{V}\cdot\text{s}} \\ &= 8.5 \times 1.6 \text{ S/cm} \\ \sigma &= 14 \text{ S/cm} \end{aligned}$$

7. A piece of silicon at room temperature (300K) is doped with donors to $N_D = 10^{17} \text{ cm}^{-3}$. The sample is uniformly illuminated with a generation rate of EHPs: $g_{\text{opt}} = 10^{22} \text{ cm}^{-3} \text{ s}^{-1}$. (a) what is the excess carrier concentration p' (or n')? (b) what is the *total* concentration of electrons? (c) what is the *total* concentration of holes?

$$a) \quad n' = p' = g_{\text{opt}} \tau_n = 10^{22} \text{ cm}^{-3} \text{ s}^{-1} \times 10^{-6} \text{ sec}$$

$$= 10^{16} \text{ cm}^{-3}$$

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$$b) \quad n = n_0 + n' = N_D + n' = 10^{17} \text{ cm}^{-3} + 10^{16} \text{ cm}^{-3}$$

$$= 1.1 \times 10^{17} \text{ cm}^{-3}$$

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$$c) \quad p_0 = \frac{n_i^2}{N_D} = \frac{10^{20} \text{ cm}^{-6}}{10^{17}} = 10^3 \text{ cm}^{-3}$$

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$$p = p_0 + p' = 10^3 \text{ cm}^{-3} + 10^{16} \text{ cm}^{-3}$$

$$= 10^{16} \text{ cm}^{-3}$$